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(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: BUYNOSKI, Matthew, Stephen; 2607 Emerson Street, Palo Alto, CA 94036 (US). NG, Che-Hoo; 2880 Paseo Robles, San Martin, CA 95046 (US).

(74) Agent: RODDY, Richard, J.; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

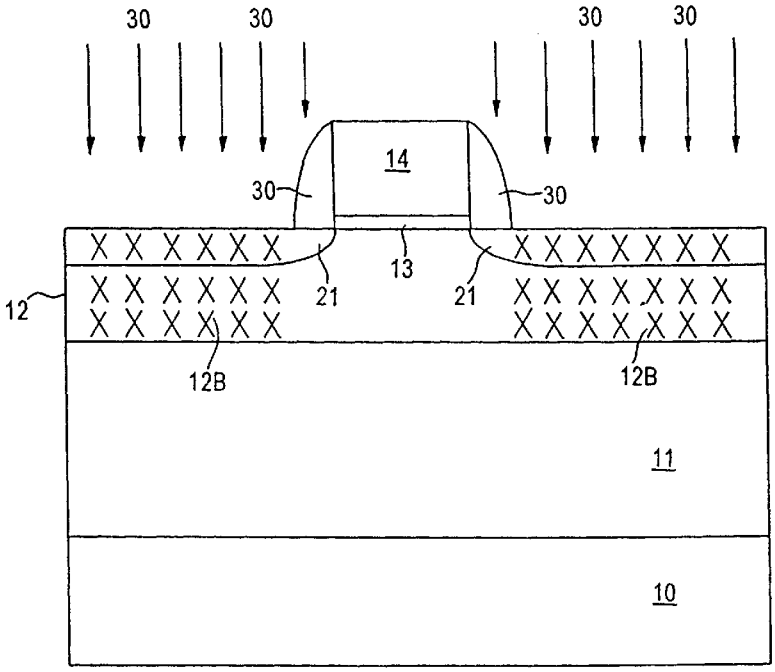
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(54) Title: XE PREAMORPHIZING IMPLANTATION



(57) Abstract: A SOI substrate (101) is preamorphized by ion implanting Xe 15 prior to forming source/drain extensions (21) and source/drain regions (41), thereby virtually eliminating or significantly reducing floating body effects. Other aspects comprise ion implanting a Xe_2^+ into a bulk silicon or SOI substrate to effect preamorphization prior to forming source/drain extensions and regions having shallow junctions with reduced vertical and lateral straggle.

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